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**Lin et al.**

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(54) **PACKAGE ON PACKAGE (POP) BONDING STRUCTURES**

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**H01L 23/498** (2006.01)  
**H01L 21/48** (2006.01)

(Continued)

(52) **U.S. Cl.**  
CPC ..... **H01L 23/49816** (2013.01); **H01L 21/486** (2013.01); **H01L 23/49827** (2013.01); **H01L 23/5389** (2013.01); **H01L 24/24** (2013.01); **H01L 24/82** (2013.01); **H01L 24/97** (2013.01); **H01L 25/105** (2013.01); **H01L 2224/0401** (2013.01); **H01L 2224/04105** (2013.01); **H01L 2224/12105** (2013.01); **H01L 2224/32145**

(2013.01); **H01L 2224/32225** (2013.01); **H01L 2224/48227** (2013.01); **H01L 2224/73265** (2013.01); **H01L 2224/97** (2013.01); **H01L 2225/0651** (2013.01); **H01L 2225/06568** (2013.01); **H01L 2225/1035** (2013.01); **H01L 2225/1058** (2013.01); **H01L 2924/12042** (2013.01); **H01L 2924/1305** (2013.01); **H01L 2924/1306** (2013.01); **H01L 2924/13091** (2013.01); **H01L 2924/15311** (2013.01); **H01L 2924/181** (2013.01); **H01L 2924/18162** (2013.01)

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USPC ..... **257/686**  
See application file for complete search history.

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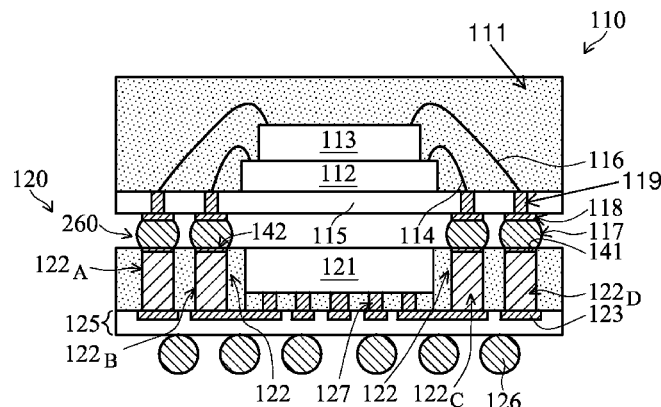
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(57) **ABSTRACT**

Various embodiments of mechanisms for forming through package vias (TPVs) with multiple conductive layers and/or recesses in a die package and a package on package (PoP) device with bonding structures utilizing the TPVs are provided. One of the multiple conductive layers acts as a protective layer of the main conductive layer of the TPVs. The protective layer is less likely to oxidize and also has a slower formation rate of intermetallic compound (IMC) when exposed to solder. The recesses in TPVs of a die package are filled by solder from the other die package and the IMC layer formed is below the surface of TPVs, which strengthen the bonding structures.

**20 Claims, 14 Drawing Sheets**



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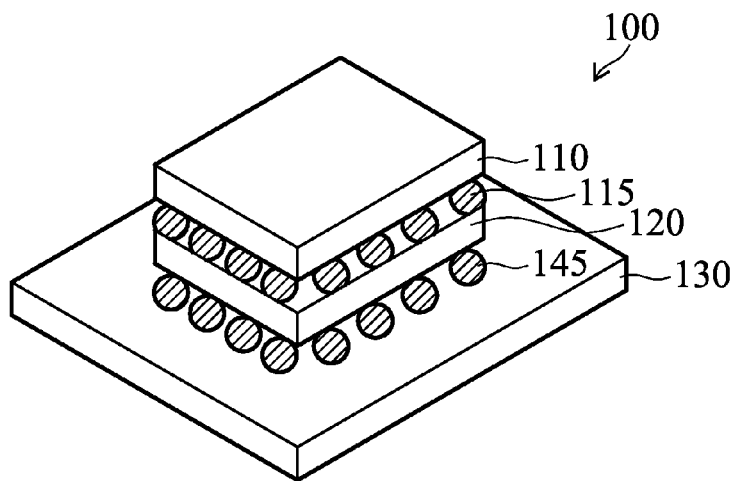


FIG. 1A

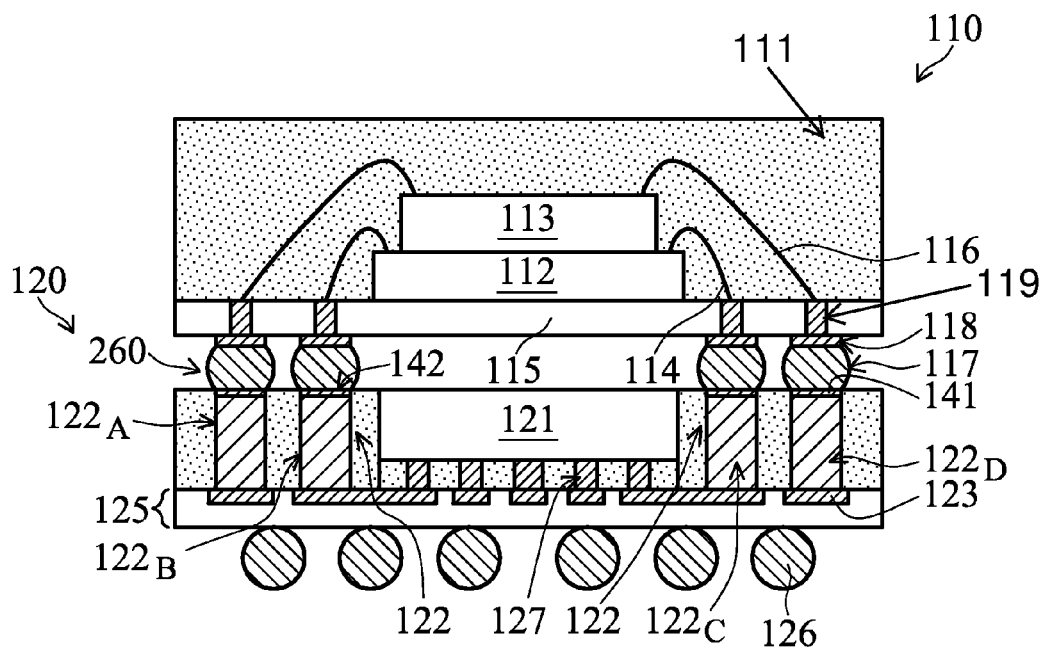


FIG. 1B



FIG. 2A

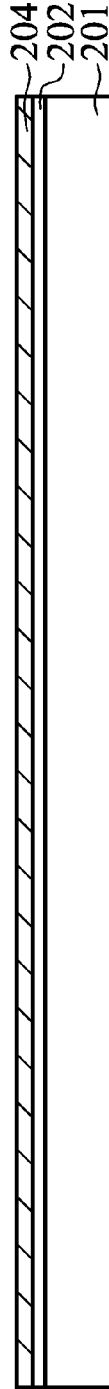


FIG. 2B

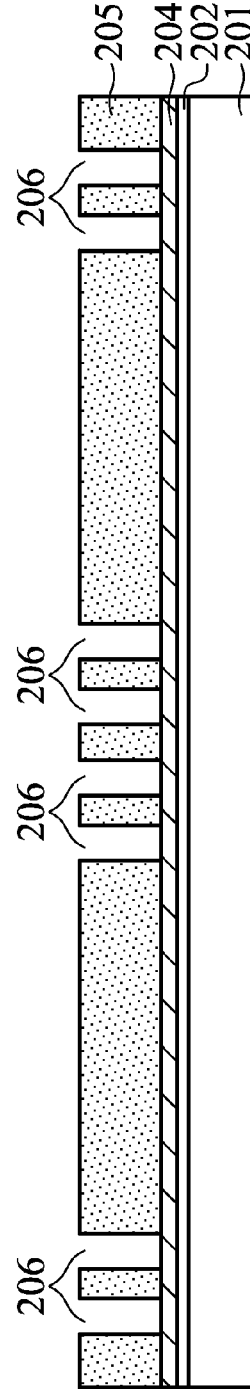


FIG. 2C

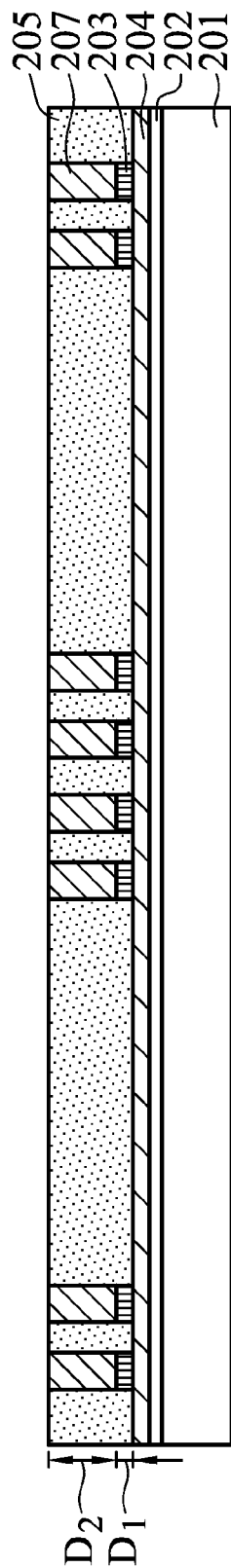


FIG. 2D

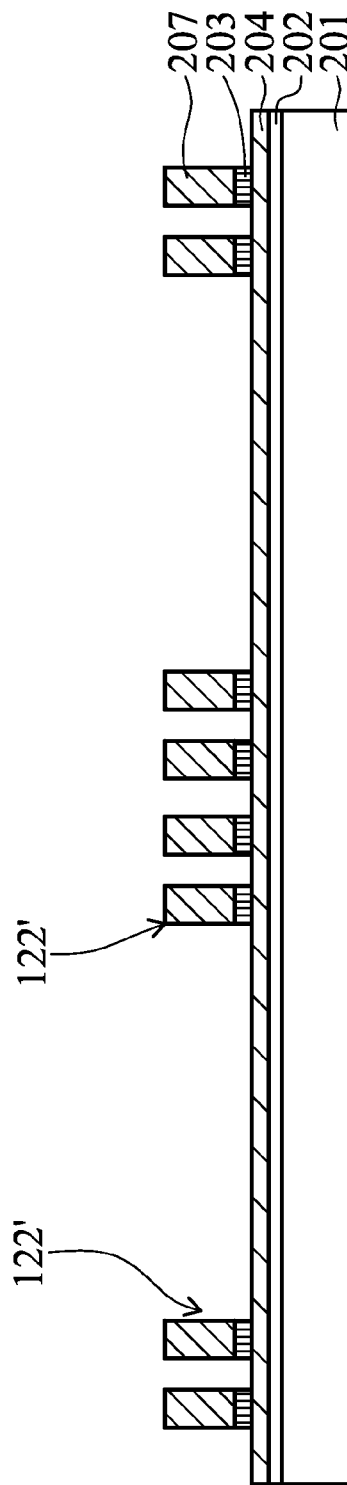


FIG. 2E

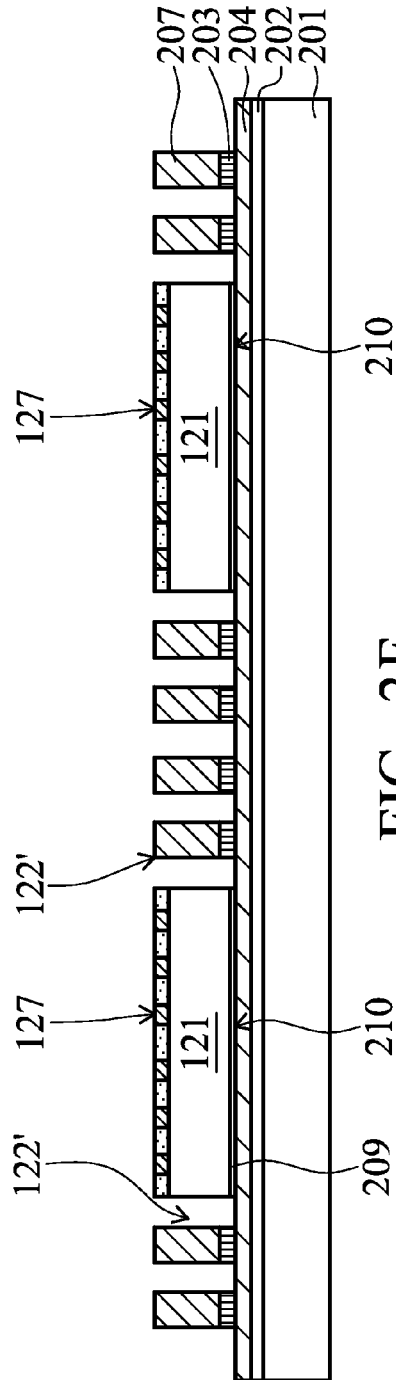


FIG. 2F

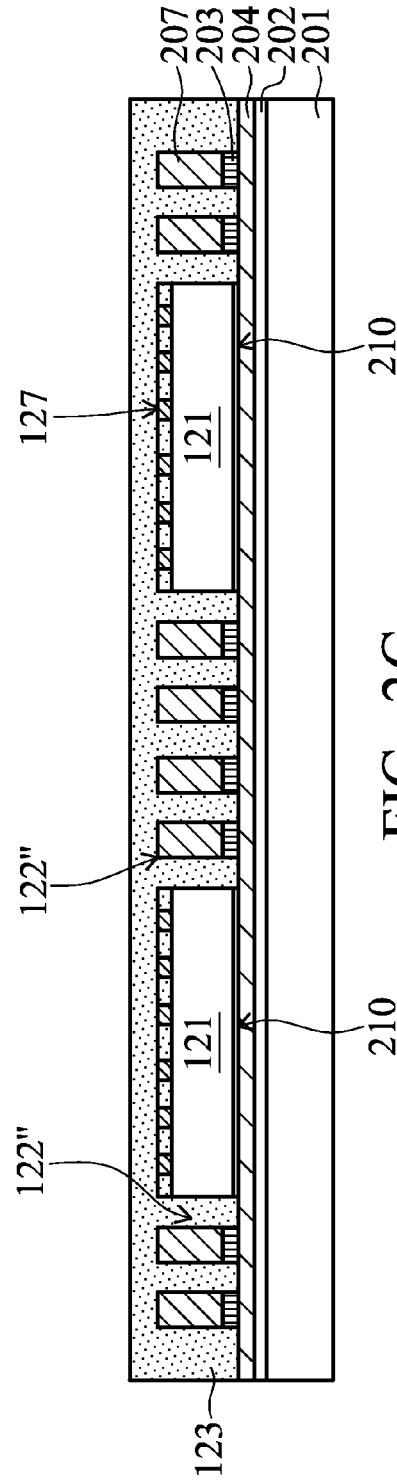


FIG. 2G

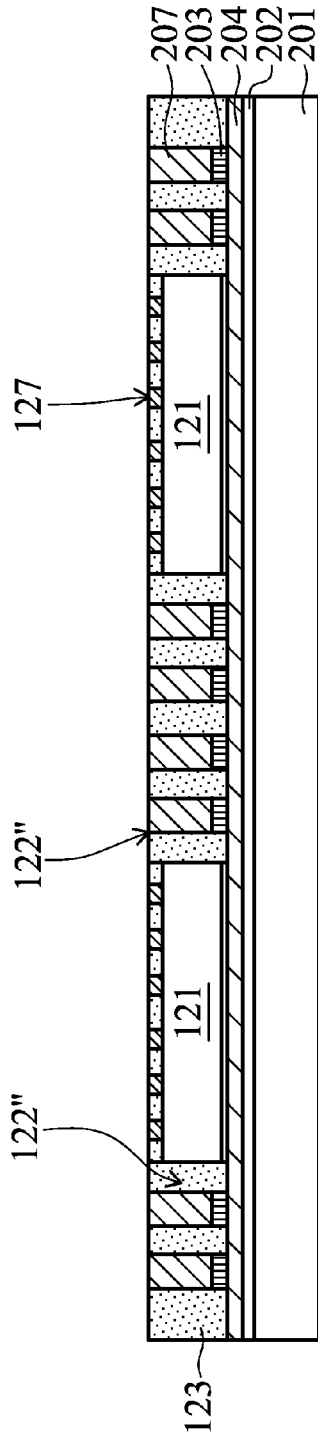


FIG. 2H

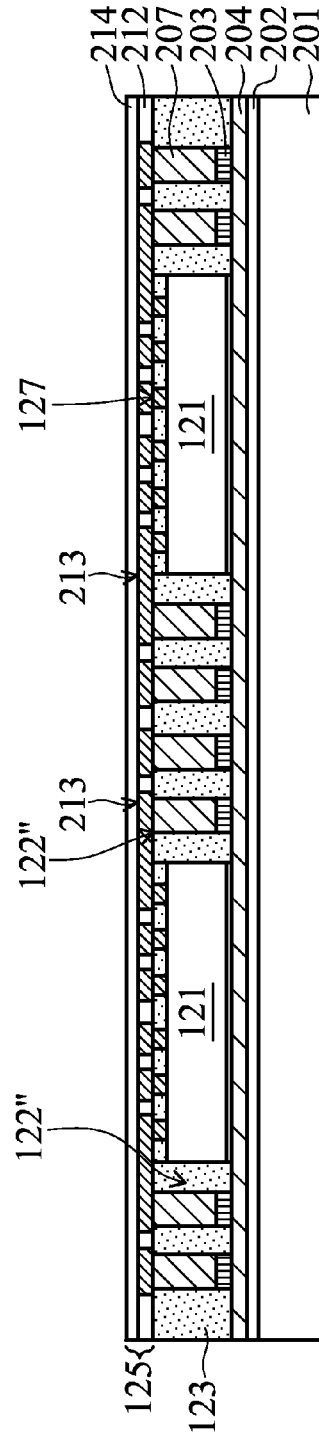


FIG. 2I

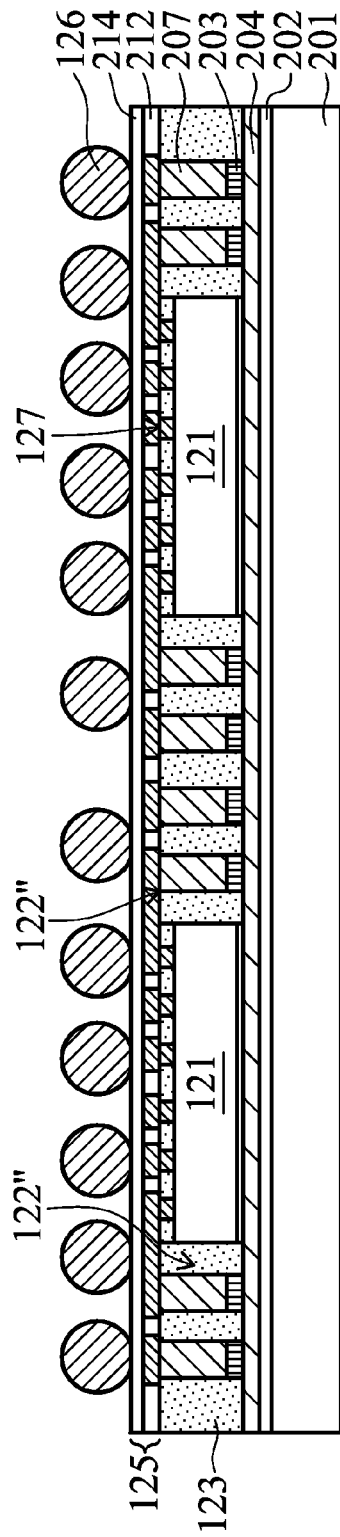


FIG. 2J

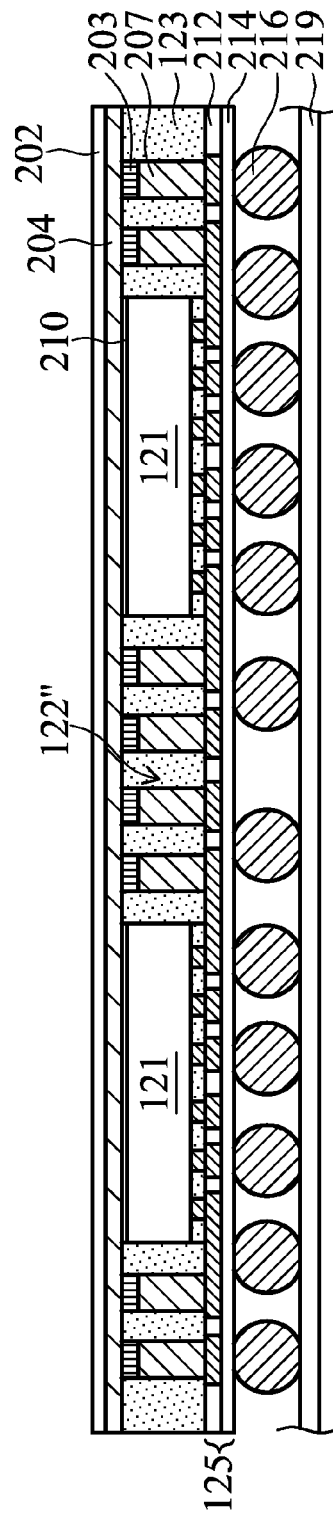


FIG. 2K



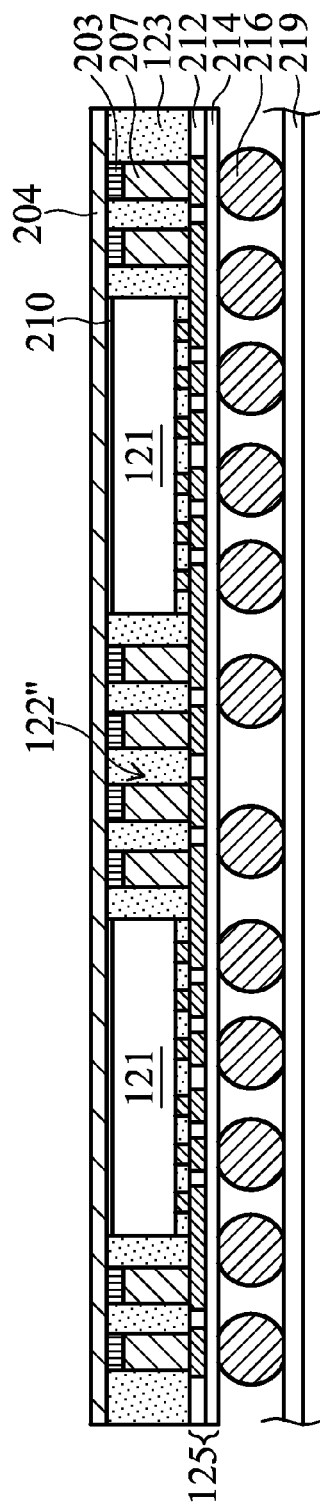


FIG. 2L

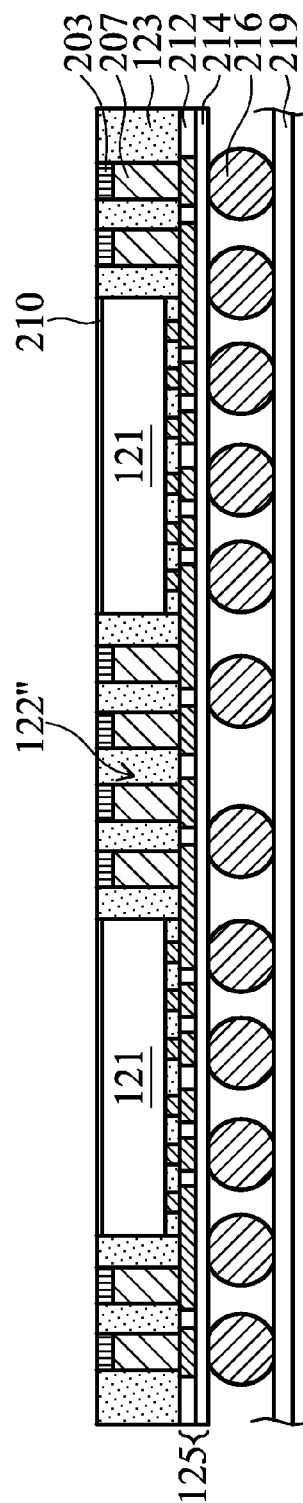


FIG. 2M

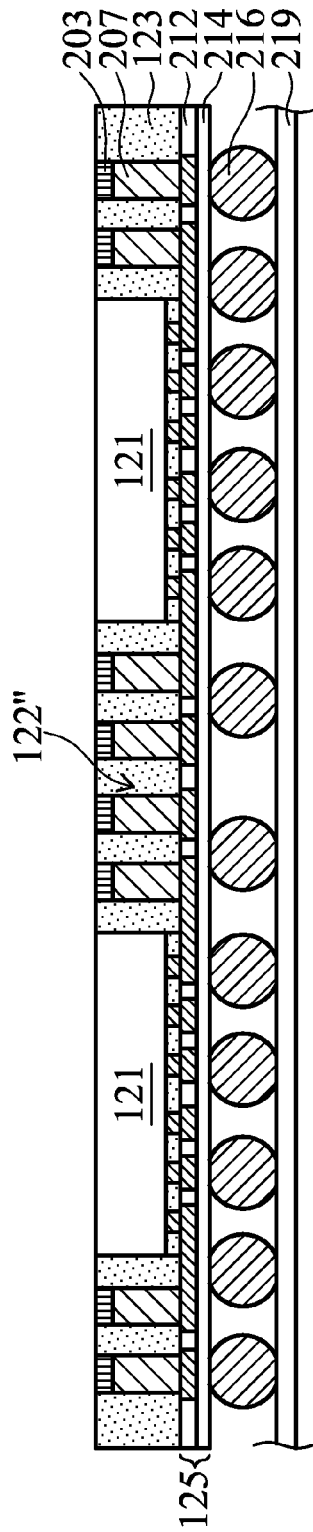


FIG. 2N

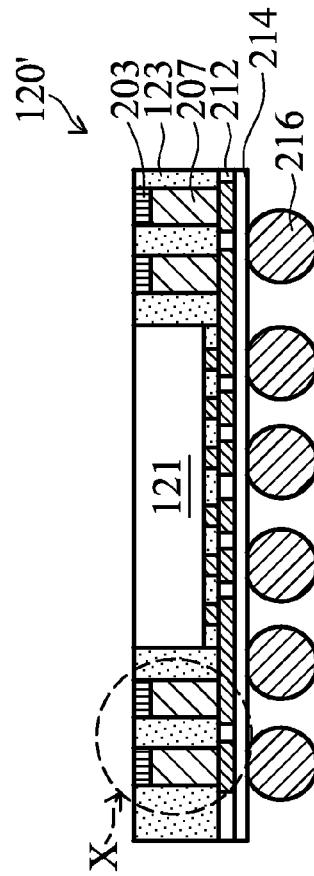


FIG. 2O

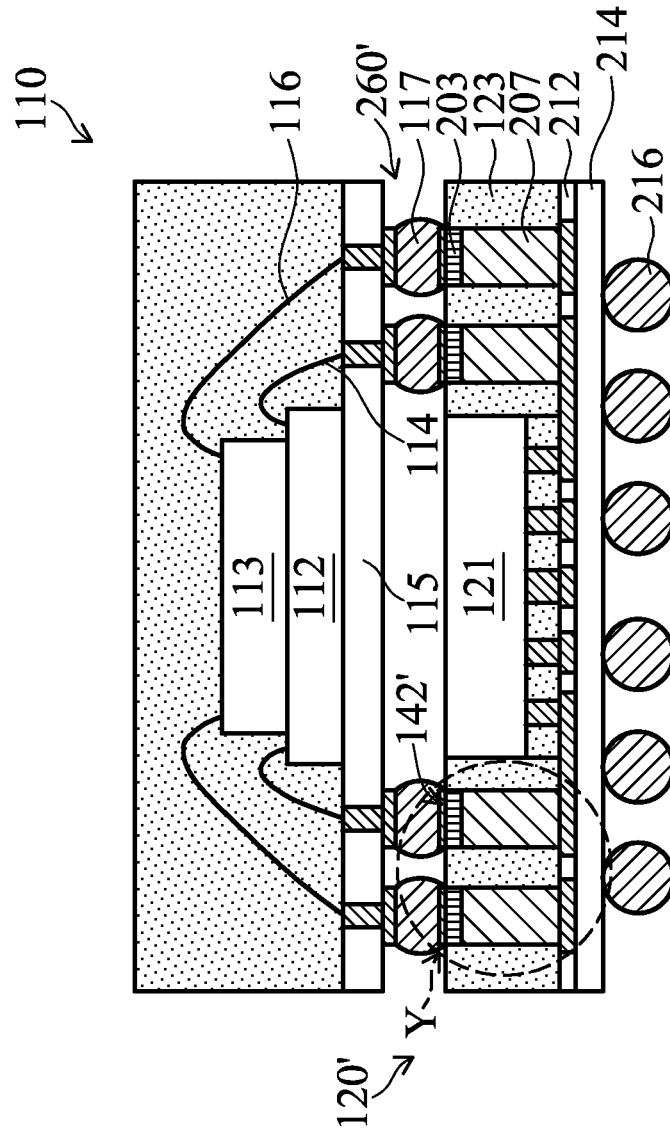


FIG. 2P

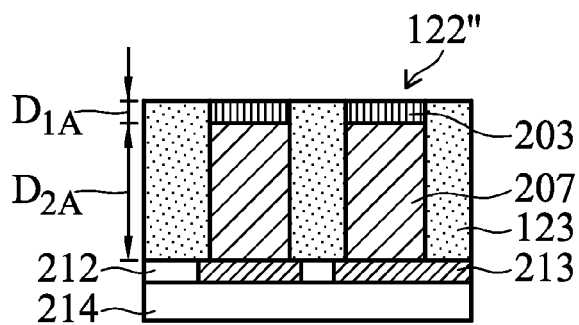


FIG. 3A

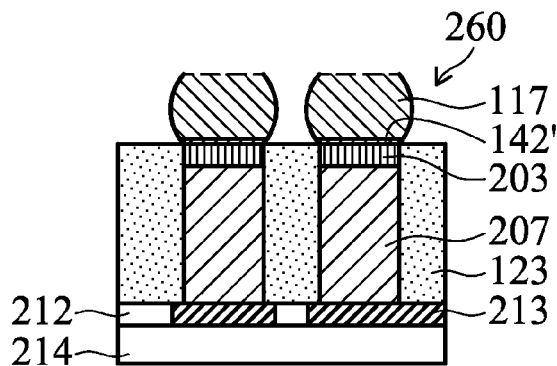


FIG. 3B

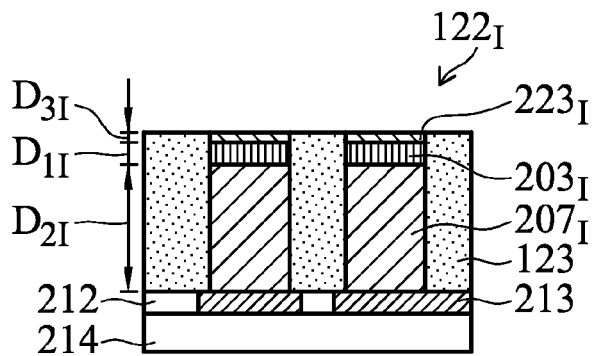


FIG. 4A

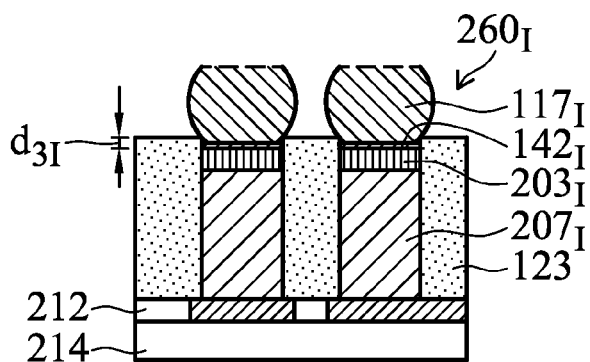


FIG. 4B

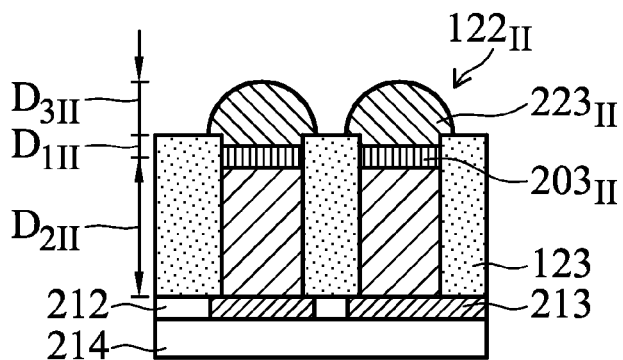


FIG. 5A

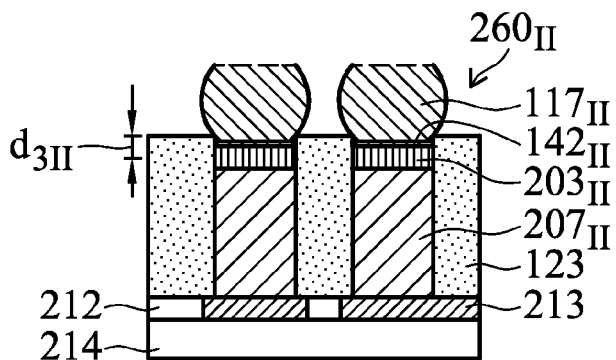


FIG. 5B

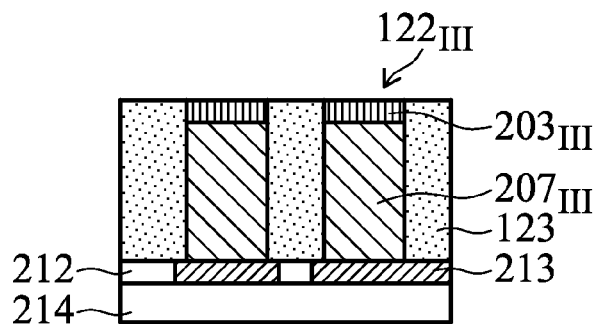


FIG. 6A

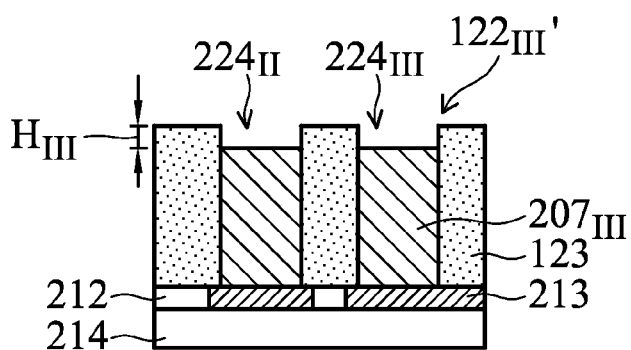


FIG. 6B

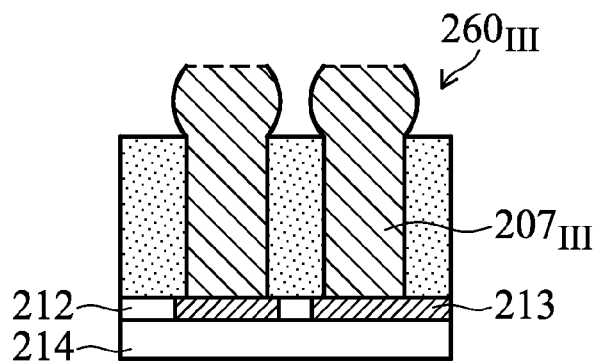


FIG. 6C

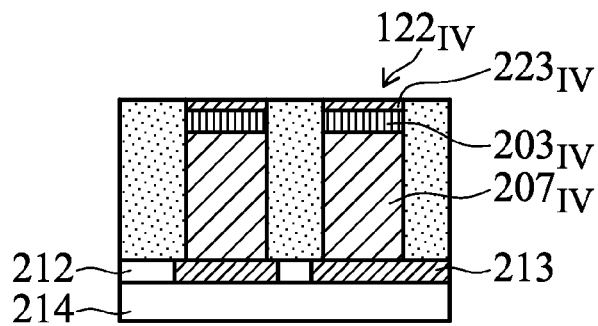


FIG. 7A

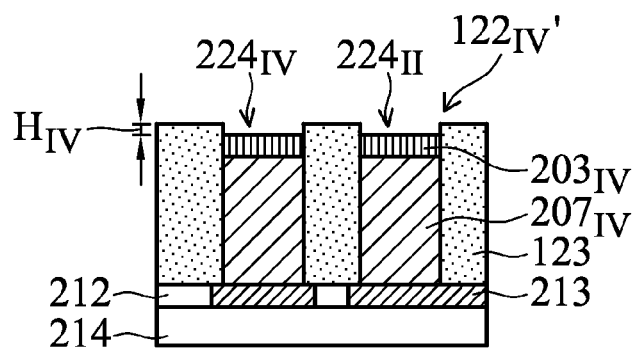


FIG. 7B

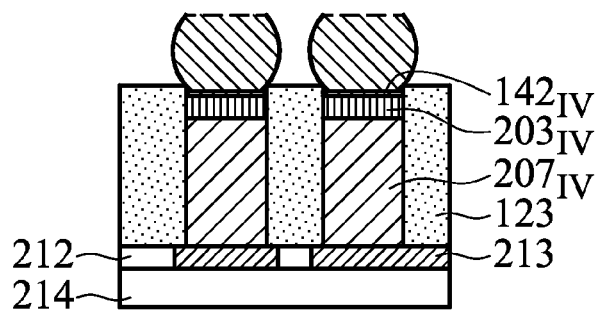


FIG. 7C

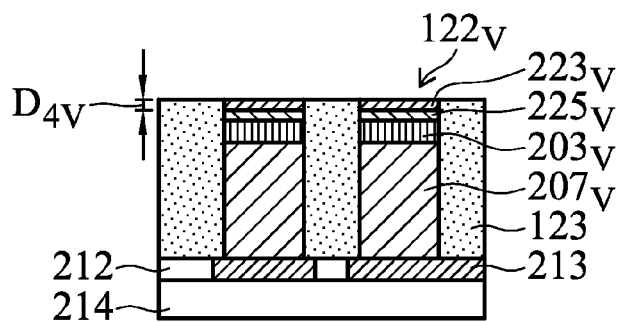


FIG. 8A

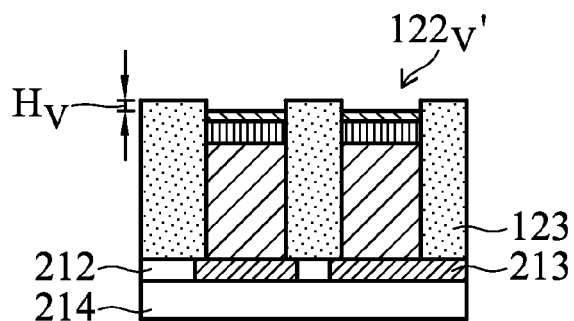


FIG. 8B

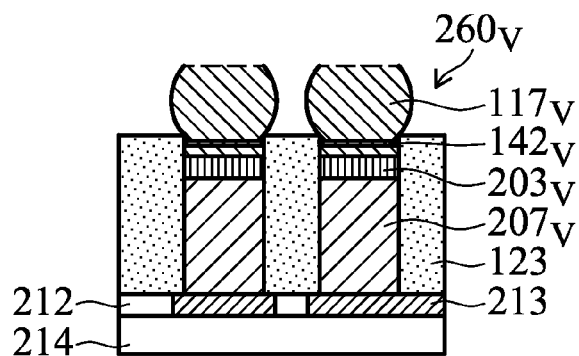


FIG. 8C



## PACKAGE ON PACKAGE (POP) BONDING STRUCTURES

This application claims the benefit of U.S. Provisional Application Ser. No. 61/746,967, filed on Dec. 28, 2012, entitled "Package on Package (PoP) Bonding Structures," which application is hereby incorporated herein by reference.

### BACKGROUND

Semiconductor devices are used in a variety of electronic applications, such as personal computers, cell phones, digital cameras, and other electronic equipment, as examples. Semiconductor devices are typically fabricated by sequentially depositing insulating or dielectric layers, conductive layers, and semiconductive layers of materials over a semiconductor substrate, and patterning the various material layers using lithography to form circuit components and elements thereon.

The semiconductor industry continues to improve the integration density of various electronic components (e.g., transistors, diodes, resistors, capacitors, etc.) by continual reductions in minimum feature size, which allow more components to be integrated into a given area. These smaller electronic components also require smaller packages that utilize less area and/or lower height than packages of the past, in some applications.

Thus, new packaging technologies, such as package on package (PoP), have begun to be developed, in which a top package with a device die is bonded to a bottom package with another device die. By adopting the new packaging technologies, the integration levels of the packages may be increased. These relatively new types of packaging technologies for semiconductors face manufacturing challenges.

### BRIEF DESCRIPTION OF THE DRAWINGS

For a more complete understanding of the embodiments, and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which:

FIG. 1A is a perspective view of a package structure, in accordance with some embodiments.

FIG. 1B show a cross-sectional view of a die package bonded to another die package, in accordance with some embodiments.

FIGS. 2A-2P show cross-sectional views of a sequential process flow of preparing a package on package (PoP) device, in accordance with some embodiments.

FIGS. 3A-8C are cross-sectional views of die packages and package-on-package (PoP) devices, in accordance with some embodiments.

### DETAILED DESCRIPTION OF ILLUSTRATIVE EMBODIMENTS

The making and using of the embodiments of the disclosure are discussed in detail below. It should be appreciated, however, that the embodiments provide many applicable inventive concepts that can be embodied in a wide variety of specific contexts. The specific embodiments discussed are illustrative, and do not limit the scope of the disclosure.

Since the invention of the integrated circuit, the semiconductor industry has experienced continual rapid growth due to continuous improvements in the integration density of various electronic components (i.e., transistors, diodes, resistors, capacitors, etc.). For the most part, this improvement in inte-

gration density has come from repeated reductions in minimum feature size, allowing for the integration of more components into a given area.

These integration improvements are essentially two-dimensional (2D) in nature, in that the volume occupied by the integrated components is essentially on the surface of the semiconductor wafer. Although dramatic improvements in lithography have resulted in considerable improvements in 2D integrated circuit formation, there are physical limits to the density that can be achieved in two dimensions. One of these limits is the minimum size needed to make these components. Also, when more devices are put into one chip, more complex designs are required.

Three-dimensional integrated circuits (3D ICs) have been therefore created to resolve the above-discussed limitations. In some formation processes of 3D ICs, two or more wafers, each including an integrated circuit, are formed. The wafers are sawed to form dies. Dies with different devices are packaged and are then bonded with the devices aligned. Through-package-vias (TPVs), also referred to as through-molding-vias (TMVs), are increasingly used as a way of implementing 3D ICs. TPVs are often used in 3D ICs and stacked dies to provide electrical connections and/or to assist in heat dissipation.

FIG. 1A is a perspective view of a package structure **100** including a package **110** bonded to another package **120**, which is further bonded to another substrate **130** in accordance with some embodiments. Each of die packages **110** and **120** includes at least a semiconductor die (not shown). The semiconductor die includes a semiconductor substrate as employed in a semiconductor integrated circuit fabrication, and integrated circuits may be formed therein and/or thereupon. The semiconductor substrate refers to any construction comprising semiconductor materials, including, but not limited to, bulk silicon, a semiconductor wafer, a silicon-on-insulator (SOI) substrate, or a silicon germanium substrate. Other semiconductor materials including group III, group IV, and group V elements may also be used. The semiconductor substrate may further comprise a plurality of isolation features (not shown), such as shallow trench isolation (STI) features or local oxidation of silicon (LOCOS) features. The isolation features may define and isolate the various microelectronic elements. Examples of the various microelectronic elements that may be formed in the semiconductor substrate include transistors (e.g., metal oxide semiconductor field effect transistors (MOSFET), complementary metal oxide semiconductor (CMOS) transistors, bipolar junction transistors (BJT), high voltage transistors, high frequency transistors, p-channel and/or n-channel field effect transistors (PFETs/NFETs), etc.); resistors; diodes; capacitors; inductors; fuses; and other suitable elements. Various processes are performed to form the various microelectronic elements including deposition, etching, implantation, photolithography, annealing, and/or other suitable processes. The microelectronic elements are interconnected to form the integrated circuit device, such as a logic device, memory device (e.g., SRAM), RF device, input/output (I/O) device, system-on-chip (SoC) device, combinations thereof, and other suitable types of devices. Package **120** includes through-package-vias (TPVs) and function as an interposer, in accordance with some embodiments.

Substrate **130** may be made of bismaleimide triazine (BT) resin, FR-4 (a composite material composed of woven fiberglass cloth with an epoxy resin binder that is flame resistant), ceramic, glass, plastic, tape, film, or other supporting materials that may carry the conductive pads or lands needed to receive conductive terminals. In some embodiments, sub-

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strate **130** is a multiple-layer circuit board. Package **110** is bonded to package **120** via connectors **115**, and package **120** is bonded to substrate **130** via external connectors **145**. In some embodiments, the external connectors **145** are bonded bump structures, such as bonded solder bumps, or bonded copper posts with a joining solder layer. Solder described here may include lead or may be lead-free.

FIG. 1B show a cross-sectional view of a die package **110** over a die package **120**, in accordance with some embodiments. As shown in FIG. 1B, package **110** includes two semiconductor dies **112** and **113**, with die **113** disposed over die **112**. However, package **110** could include one semiconductor die or more than two semiconductor dies. In some embodiments, there is a glue layer (not shown) between dies **112** and **113**. Semiconductor dies **112** and **113** may include various microelectronic elements, as described above for semiconductor dies. Semiconductor die **112** is bonded to a substrate **115**. Substrate **115** may include various materials and/or components described above for substrate **100**. Semiconductor die **112** is electrically connected to conductive elements (not shown) in substrate **115** via bonding wires **114**, in accordance with some embodiments. Similarly, semiconductor die **113** is electrically connected to the conductive elements in substrate **115** via bonding wires **116**. Package **110** also includes a molding compound **111**, which covers semiconductor dies **112** and **113**, and also bonding wires **114** and **116**. Package **110** also includes a number of connectors **117** for external connections. Connectors **117** are formed on metal pads **118**, which are electrically connected to bonding wires **114** and **116** by interconnect structures **119**, which may include vias and metal lines.

Die package **120** includes a semiconductor die **121** and TPVs **122**, which surround die **121**, as shown in FIG. 1B in accordance with some embodiments. Package **120** also includes a redistribution structure **125**, which includes one or more redistribution layers (RDLs) **123**. Redistribution layers (RDLs) **123** are metal interconnect layers, which may include metal lines and vias, and are surrounded by dielectric material(s). RDL(s) **123** enables fan-out of die **121**. External connectors **126**, such as ball grid array (BGA), are attached to metal pads (not shown) on redistribution structure **125**, as shown in FIG. 1B. As shown in FIG. 1B, TPVs **122** are connected to connectors **117** of package **110**. Die **121** and external connectors **126** are on opposite sides of redistribution structure **125**. Die **121** is connected to redistribution structure **125** via connectors **127**.

Connectors **117** of die package **110** are made of solders, in some embodiments. In some embodiments, connectors **117** include copper posts with solder at the ends of solder posts. The solder of connectors **117** are bonded to exposed copper surface of TPVs **122**, which are filled with copper. However, the exposed copper surface could form copper oxide when exposed to atmosphere. As a result, a copper oxide layer **141**, as shown in TPV **122<sub>D</sub>** of FIG. 1B, could form on the surface of TPVs **122**. Although a flux could be applied on the surface of TPVs **122** to remove the copper oxide layer formed on the surface of TPVs **122**, the removal process is non-consistent in some embodiments. As a result, copper oxide layer **141**, or at least a portion of copper oxide layer **141**, remains on some TPVs **122**, such as TPV **122<sub>D</sub>**. Solder of connectors **126** does not bond well to copper oxide layer **141**; therefore, the joint would be weak, which would affect yield and reliability.

Even if flux does remove the copper oxide layer from TPVs, such as TPVs **122<sub>A</sub>**, **122<sub>B</sub>**, and **122<sub>C</sub>**, the direct contact between solder of connectors **126** and copper of TPVs would result in the formation of intermetallic compound (IMC), such as Cu:Sn. FIG. 1B shows IMC layer **142** formed

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between solder of connectors **126** and copper of TPVs **122<sub>A</sub>**, **122<sub>B</sub>**, and **122<sub>C</sub>**, in accordance with some embodiments. Due to varying coefficients of thermal expansion (CTEs) of different elements on package **120**, package **120** could bow during and/or after packaging process. Such bowing (or warpage) creates stress for the bonding structures, formed by bonded connectors **126** and TPVs **122**, between package **120** and package **110**. The stress could cause cracking of the bonding structures **260**, formed by connectors **117** and TPVs **122**, to affect yield and reliability of the package-on-package (PoP) structure.

A protective layer (not shown), such as a solder paste layer, an organic solderability paste layer (OSP), or other applicable protective layer, could be formed over TPVs **122** after they are exposed and before they are bonded to connectors. However, forming such a protective layer after the formation of TPVs **122** could involve transferring the carrier with the packaged dies (or the substrate) to a processing system or chamber and/or processing the substrate to form the protective layer. Prior to forming the protective layer, surfaces of the TPVs **122** would need to be treated, such as by flux, to remove the oxide layer **141** formed. Such additional processing operations could be cost-prohibiting. Consequently, there is a need of mechanisms for forming bonding structures between die packages without the issues described above.

FIGS. 2A-2P show cross-sectional views of a sequential process flow of preparing a package on package (PoP) device, in accordance with some embodiments. FIG. 2A shows an adhesive layer (or glue layer) **202**, which is over carrier **201**. Carrier **201** is made of glass, in accordance with some embodiments. However, other materials may also be used for carrier **201**. Adhesive layer **202** is deposited or laminated over carrier **201**, in some embodiments. Adhesive layer **202** may be formed of a glue, or may be a lamination material, such as a foil. In some embodiments, adhesive layer **202** is photosensitive and is easily detached from carrier **201** by shining ultra-violet (UV) light or laser on carrier **201** after the involved packaging process is completed **120**. For example, adhesive layer **202** may be a light-to-heat-conversion (LTHC) coating made by 3M Company of St. Paul, Minn. In some other embodiments, the adhesive layer **202** is heat-sensitive. In some embodiments, there is a glue layer (not shown) adhesive layer **202**. For example, the glue layer could be a die attach film (DAF), a polymer (such as polyimide or polybenzoxazole (PBO)), or a solder resist to improve adhesion.

A plating seed layer **204** is then formed on the adhesive layer **202**, as shown in FIG. 2B in accordance with some embodiments. In some embodiments, the plating seed layer **204** is made of copper and is formed by physical vapor deposition (PVD). However, other conductive film may also be used. For example, the plating seed layer **204** may be made of Ti, Ti alloy, Cu, and/or Cu alloy. The Ti alloy and Cu alloy may include silver, chromium, nickel, tin, gold, tungsten, and combinations thereof. In some embodiments, the thickness of the plating seed layer **204** is in a range from about 0.1  $\mu\text{m}$  to about 1.0  $\mu\text{m}$ . In some embodiments, the plating seed layer **204** includes a diffusion barrier layer, which is formed prior to the deposition of the plating seed layer. The plating seed layer **204** may also act as an adhesion layer to under layer. In some embodiments, the diffusion barrier layer is made of Ti with a thickness in a range from about 0.01  $\mu\text{m}$  to about 0.1  $\mu\text{m}$ . However, the diffusion barrier layer may be made of other materials, such as TaN, or other applicable materials and the thickness range is not limited to the range described above. The diffusion barrier layer is formed by PVD in some embodiments.

Following the deposition of the plating seed layer **204**, a photoresist layer **205** is formed over plating seed layer **204**, as shown in FIG. 2C in accordance with some embodiments. The photoresist layer **205** may be formed by a wet process, such as a spin-on process, or by a dry process, such as by a dry film. After the photoresist layer **205** is formed, the photoresist layer **205** is patterned to form openings **206**, which are filled to form TPVs described above in FIG. 1B. The processes involved include photolithography and resist development. In some embodiments, the width W of openings **206** is in a range from about 40  $\mu\text{m}$  to about 260  $\mu\text{m}$ . In some embodiments, the depth D of openings **206** is in a range from about 60  $\mu\text{m}$  to about 300  $\mu\text{m}$ .

Afterwards, a first conductive layer **203** is plated on the surface of plating seed layer **204**, in accordance with some embodiments. The first conductive layer **203** does not form IMC with solder, or forms IMC with solder at a much slower rate than copper. In addition, the first conductive layer **203** is less or much less likely to oxidize than copper when exposed to the environment (e.g., air). In some embodiments, the first conductive layer **203** is made of nickel (Ni). However, other conducting material possessing the quality described above for layer **203**, such as platinum (Pt), gold (Au), silver (Ag), Tin (Sn), Sn alloy (including, but are not limited to, SnAg, SnAgCu, SnCu, SnAgCu—Bi), etc., and combinations thereof may also be used. In some embodiments, the thickness of layer **203**,  $D_1$ , is in a range from about 0.1  $\mu\text{m}$  to about 30  $\mu\text{m}$ .

Following the formation of the first conductive layer **203**, a second conductive layer **207** is plated over the first conductive layer **203** to fill openings **206**, as shown in FIG. 2D in accordance with some embodiments. In some embodiments, the thickness of layer **207**,  $D_2$ , is in a range from about 50  $\mu\text{m}$  to about 300  $\mu\text{m}$ .

Following the plating to gap-fill process, the photoresist layer **205** is removed by an etching process, which may be a dry or a wet process. FIG. 2E shows a cross-sectional view of the structure on carrier **201** after the photoresist layer **205** is removed and conductive material in the openings **206** are exposed as (conductive) columns **122'**, in accordance with some embodiments.

Afterwards, semiconductor die **121** is attached to a surface **209** over carrier **201** by a glue layer **210**, as shown in FIG. 2F in accordance with some embodiments. Glue layer **210** is made of a die attach film (DAF), in accordance with some embodiments. DAF may be made of epoxy resin, phenol resin, acrylic rubber, silica filler, or a combination thereof. FIG. 2F show that connectors **127** of die **121** are facing away from the surface **209**. A liquid molding compound material is then applied on the surface of plating seed layer **204** over carrier **201** to fill the space between conductive columns **122'** and die **121** and to cover die **121** and conductive columns **122'**. In some embodiments, semiconductor die **121** is attached directly on the surface of layer **202**. Layer **204** under die **121** is first removed. Under such circumstance, the molding compound is applied on the surface of layer **202**. A thermal process is then applied to harden the molding compound material and to transform it into molding compound **123**. Conductive columns **122'** become TPVs **122"** after the molding compound **123** is formed to surround them.

Afterwards, a planarization process is applied to remove excess molding compound **123** to expose TPVs **122"** and connectors **127** of die **121**, as shown in FIG. 2G in accordance with some embodiments. In some embodiments, the planarization process is a grinding process. In some other embodiments, the planarization process is a chemical-me-

chanical polishing (CMP) process. The post planarization structure is shown in FIG. 2H in accordance with some embodiments.

Following the planarization process, redistribution structure **125** is formed over surface **211** over structure of FIG. 2H, as shown in FIG. 2I in accordance with some embodiments. FIG. 2I shows that the second redistribution structure **125** include RDLs **213**, which are insulated by one or more passivation layers, such as layer **212** and **214**. RDLs **213** may include metal lines and conductive vias. The RDLs **213** are made of a conductive material and directly contacts TPVs **122"** and connectors **127** of die **121**. In some embodiments, the RDLs **213** are made of aluminum, aluminum alloy, copper, or copper-alloy. However, RDLs **213** may be made of other types of conductive materials. The passivation layers **212** and **214** are made of dielectric material(s) and provide stress relief for bonding stress incurred during bonding external connectors **126** with substrate **130**. In some embodiments, the passivation layers **212** and **214** are made of polymers, such as polyimide, polybenzoxazole (PBO), or benzocyclobutene (BCB). Passivation **214** is patterned to form openings (not shown) to expose portions of RDLs **123** to form bond pads (not shown). In some embodiments, a under bump metallurgy (UBM) layer (not shown) is formed over bond pads. The UBM layer may also line the sidewalls of openings of passivation layer **214**. The RDLs **213** may be a single layer, in some embodiments.

Examples of redistribution structures and bonding structures, and methods of forming them are described in U.S. application Ser. No. 13/427,753, entitled "Bump Structures for Multi-Chip Packaging," filed on Mar. 22, 2012, and U.S. application Ser. No. 13/338,820, entitled "Packaged Semiconductor Device and Method of Packaging the Semiconductor Device," filed on Dec. 28, 2011. Both above-mentioned applications are incorporated herein by reference in their entireties.

After the redistribution structure **125** is formed, external connectors **126** are mounted on (or bonded to) bond pads (not shown) of redistribution structure **125**, as shown in FIG. 2J in accordance with some embodiments. The dies on carrier **201** are electrically tested to check for the functionality of dies and also for the quality of the formation of the TPVs **122"**, the redistribution structure **125** and bonded external connectors **126**. In some embodiments, reliability test is also performed.

After external connectors **126** are mounted on bond pads, the structure in FIG. 2J is flipped and is attached to a tape **219**, as shown in FIG. 2K in accordance with some embodiments. Tape **219** is photosensitive and is easily detached from carrier **201** by shining ultra-violet (UV) light on carrier **201** after the involved packaging process is completed in accordance with some embodiments. Afterwards, carrier **201** and adhesive layer **202** are removed. Laser could be used to provide heat to remove the adhesive layer. FIG. 2L shows the structure after carrier **201** and adhesive layer **202** are removed. Following the removal of the adhesive layer **202**, the plating seed layer **204** is removed, as shown in FIG. 2M in accordance with some embodiments. The plating seed layer **204** is removed by etching, such as by a wet etch. To remove copper, an aqueous solution with phosphoric acid ( $\text{H}_3\text{PO}_4$ ) and hydrogen peroxide ( $\text{H}_2\text{O}_2$ ) may be used. If the plating seed layer **204** includes a diffusion barrier layer, such as a Ti layer, an aqueous solution of HF can be used. In some embodiments, a portion of first conductive layer **203** is removed to form a recess (not shown) in each TPV **122"**.

Following the removal of the plating seed layer **204**, glue layer **210** is removed as shown in FIG. 2N, in accordance with some embodiments. As mentioned above, glue layer **210** may

be made of a die attach film (DAF), which could be removed by a wet stripping process containing tetramethylammonium hydroxide (TMAH) and dimethyl sulfoxide (DMSO). In some embodiments, the glue layer 210 is not removed and stays to assist in dissipating heat generated by die 121.

Whether the glue layer 210 is removed or not (depending on the requirement), the packed die is then singulated into individual packaged dies. The singulation is accomplished by die saw. After singulation is completed, tape 219 is removed from the packaged dies. FIG. 2O shows a packaged die 120' following the removal of tape 210, in accordance with some embodiments. Region X in FIG. 2O includes two TPVs 122 in the illustrated example.

A die package 110 is then placed over die package 120'. External connectors 117 of die package 110 are bonded to TPVs 122' of die package 120', as shown in FIG. 2P in accordance with some embodiments. Due to the insertion of the first conductive layer 203, the bonding structures 260' formed by connectors 117 and TPVs 122' have a thinner IMC layer 142', which is formed by solder from connectors 117 and a conductive material, such as Ni. The IMC, such as Ni:Sn, is formed at a rate slower than IMC of solder and copper (Cu:Sn). Region Y in FIG. 2P shows bonding structures 260' and IMC layer 142'.

FIG. 3A shows an enlarged view of region X of FIG. 2O, in accordance with some embodiments. Region X includes TPVs 122'', which are surrounded by molding compound 123. TPVs 122'' are connected to RDL 213, which is insulated by passivation layers 212 and 214. Each of TPVs 122'' has a first conductive layer 203 with a height  $D_{1A}$  and a second conductive layer 207 with a height  $D_{2A}$ .  $D_{1A}$  is in a range from about 0.5  $\mu\text{m}$  to about 10  $\mu\text{m}$ , in some embodiments.  $D_{2A}$  is in a range from about 50  $\mu\text{m}$  to about 300  $\mu\text{m}$ , in some embodiments. FIG. 3B shows an enlarged view of region Y of FIG. 2Q, in accordance with some embodiments. FIG. 3B shows that an IMC layer 142' is formed between Sn of solder and the first conductive layer 203. For example, if the first conductive layer 203 is made of Ni, a Ni:Sn-containing IMC is formed. In some embodiments, the thickness of IMC layer 142' is in a range from about 0.5  $\mu\text{m}$  to about 10  $\mu\text{m}$ , in some embodiments. IMC layer 142' is much thinner than IMC layer 142 (containing Cu:Sn) described in FIG. 1B. Therefore, the first conductive layer 203 acts as a protective layer of the second (or main) conductive layer 207 of TPVs 122''.

Further, because the first conductive layer 203 is less likely or very unlikely to oxidize, the risk of forming an interfacial oxide layer similar to oxide layer 141 of FIG. 1B is greatly reduced, in many cases reduced to none. If a flux pre-treatment prior to bonding with connectors 117 is used, it would remove the surface oxide layer, if any, more consistently. As a result, the bonding structures 260 formed between die packages 110 and 120' are much stronger than the bonding structures without the first conductive layer 203. The first conductive layer 203 can be formed in an integrated plating system for forming the second conductive layer 207. The additional cost of forming the first conductive layer 203 is more reasonable and manufacturing-worthy.

The concept of forming a protective conductive layer, such as layer 203, as part of TPVs to reduce surface oxidation of TPVs and to reduce the amount of IMC formed described above may be expanded to include other types of embodiments. FIG. 4A shows TPVs 122<sub>r</sub>, in accordance with some embodiments. FIG. 4A shows that a third conductive layer 223<sub>r</sub> is formed next to the first conductive layer 203<sub>r</sub>, which is formed next to the second conductive layer 207<sub>r</sub>. In the process flow described above, the third conductive layer 223<sub>r</sub> is plated over plating seed layer 204 prior to the plating of the

first conductive layer 203<sub>r</sub>. FIG. 4B shows TPVs 122<sub>r</sub> bonded to connectors 117 to form bonding structures 260<sub>r</sub>, in accordance with some embodiments.

The third conductive layer 223<sub>r</sub> is made of solder. Having a solder layer (layer 223<sub>r</sub>) in TPVs 122<sub>r</sub> enables formation of bonded solder of bonding structures 260<sub>r</sub> to extended below the surface of molding compound 123, which moves the IMC layer 142<sub>r</sub> from near surfaces of TPVs 122<sub>r</sub> to below the surface of TPVs 122<sub>r</sub>. Moving the IMC layer 142<sub>r</sub> below the surfaces TPVs 122<sub>r</sub> strengthen the bonding structures 260<sub>r</sub>. The thicknesses of first conductive layer,  $D_{1r}$ , the thickness of second conductive layer,  $D_{2r}$ , and the thickness of the IMC layer 142<sub>r</sub> are similar to those described in FIGS. 3A and 3B, in accordance with some embodiments. The thickness of third conductive layer  $D_{3r}$  is in a range from about 0.5  $\mu\text{m}$  to about 30  $\mu\text{m}$ , in some embodiments. The depth,  $d_{3r}$ , of joint solder 117<sub>r</sub> of FIG. 4B is below the surface of molding compound 123 in a range from about 0.5  $\mu\text{m}$  to about 30  $\mu\text{m}$ , in some embodiments.  $d_{3r}$  is about the same as  $D_{3r}$ .

FIG. 5A shows TPVs 122<sub>rr</sub>, in accordance with some embodiments. FIG. 5A shows that a third conductive layer 223<sub>rr</sub> is formed over the first conductive layer 203<sub>rr</sub>. As described above in FIG. 2M, a portion of first conductive layer is removed to form a recess (not shown) in each TPV. If the structure of FIG. 3A is used to form the structure of FIG. 5A, an etch chemistry for removing the first conductive layer 203<sub>rr</sub>, such as Ni, is used to form the recess. If the structure of FIG. 4A is used to form the structure of FIG. 5A, an etch chemistry for removing solder is used to form the recess. The third conductive layer 223<sub>rr</sub>, such as a solder paste, is applied to fill the recess. As shown in FIG. 5A, some of the third conductive layer 223<sub>rr</sub> protrudes above TPVs 122<sub>rr</sub>. FIG. 5B shows TPVs 122<sub>rr</sub> bonded to connectors 117 to form bonding structures 260<sub>rr</sub>, in accordance with some embodiments.

The third conductive layer 223<sub>rr</sub> is made of solder. Similar to the structures of FIGS. 4A and 4B, having a solder layer (layer 223<sub>rr</sub>) in TPVs 122<sub>rr</sub> enables formation of bonded solder of bonding structures 260<sub>rr</sub> to extended below the surface of molding compound 123, which moves the IMC layer 142<sub>rr</sub> from near surfaces of TPVs 122<sub>rr</sub> to below the surface of TPVs 122<sub>rr</sub>. The thicknesses of first conductive layer,  $D_{1rr}$ , the thickness of second conductive layer,  $D_{2rr}$ , and the thickness of the IMC layer 142<sub>rr</sub> are similar to those described in FIGS. 3A and 3B, in accordance with some embodiments. The thickness of third conductive layer  $D_{3rr}$  is in a range from about 0.5  $\mu\text{m}$  to about 30  $\mu\text{m}$ , in some embodiments. The height of recess portion  $H_{rr}$  is in a range from about 0.5  $\mu\text{m}$  to about 30  $\mu\text{m}$ , in some embodiments. The depth,  $d_{3rr}$ , of joint solder 117<sub>rr</sub> of FIG. 5B is below the surface of molding compound 123 in a range from about 0.5  $\mu\text{m}$  to about 30  $\mu\text{m}$ , in some embodiments.

FIG. 6A shows TPVs 122<sub>mr</sub>, in accordance with some embodiments. TPVs 122<sub>mr</sub> are similar to TPVs 122'' of FIG. 3A. However, the second conductive layer 207<sub>mr</sub> is made of solder, not copper, and the first conductive layer 203<sub>mr</sub> is made of Cu or Ti. Solder is cheaper than copper and has good conductivity. Manufacturing cost can be reduced by using solder as the second conductive layer. First conductive layer 203<sub>mr</sub>, made of Cu or Ti, is removed by etching when during the removal of plating seed layer 204, as described above in FIG. 2M. The chemistry used to etch plating seed layer 204 can be used to remove the first conductive layer 203<sub>mr</sub>. FIG. 6B shows TPVs 122<sub>mr</sub>' after the first conductive layer 203<sub>mr</sub> is removed, in accordance with some embodiments. Recesses 224<sub>mr</sub> are formed. The height  $H_{mr}$  of recesses 224<sub>mr</sub> is in a range from about 0.5  $\mu\text{m}$  to about 30  $\mu\text{m}$ , in some embodiments.

TPVs **122<sub>III</sub>**' are bonded to connectors **117** to form bonding structures **260<sub>III</sub>**, as shown in FIG. 6C in accordance with some embodiments. Solder from connectors **117** fills the recess near the surface of TPVs **122<sub>III</sub>**'.

FIG. 7A shows TPVs **122<sub>IV</sub>**, in accordance with some embodiments. TPVs **122<sub>IV</sub>** are similar to TPVs **122<sub>I</sub>** of FIG. 4A. First conductive layer **203<sub>IV</sub>** is similar to first conductive layer **203<sub>I</sub>**. Second conductive layer **207<sub>IV</sub>** is similar to second conductive layer **207<sub>I</sub>**. However, the third conductive layer **223<sub>IV</sub>** is made of copper or Ti, not solder. The third conductive layer **223<sub>IV</sub>**, made of Cu or Ti, is removed by etching when during the removal of plating seed layer **204**, as described above for FIG. 2M. The chemistry used to etch plating seed layer **204** can be used to remove the first conductive layer **203<sub>IV</sub>**. FIG. 7B shows TPVs **122<sub>IV</sub>**' after the third conductive layer **223<sub>IV</sub>** is removed, in accordance with some embodiments. In some embodiments, a thin layer of third conductive layer **223<sub>IV</sub>** remains over **203<sub>IV</sub>**. Recesses **224<sub>IV</sub>** is formed after the complete or partial removal of third conductive layer **223<sub>IV</sub>**. The height  $H_{IV}$  of recesses **224<sub>IV</sub>** is in a range from about 0.5  $\mu\text{m}$  to about 30  $\mu\text{m}$ , in some embodiments.

TPVs **122<sub>IV</sub>**' are bonded to connectors **117** to form bonding structures **260<sub>IV</sub>**, as shown in FIG. 7C in accordance with some embodiments. Solder from connectors **117** fills the recess near the surface of TPVs **122<sub>IV</sub>**'. If a thin layer of third conductive layer **223<sub>IV</sub>** remains in TPVs **122<sub>IV</sub>**' and is oxidized, the oxidized layer may be removed by an etch process, by flux, or dissolve in solder after bonding. FIG. 7C shows that an IMC later **142<sub>IV</sub>** is formed between the first conductive layer **203<sub>IV</sub>** and solder of connectors **117**, in accordance with some embodiments. The thickness range of IMC layer **142<sub>IV</sub>** is similar to IMC layer **142'** of FIG. 3B.

FIG. 8A shows TPVs **122<sub>V</sub>**, in accordance with some embodiments. TPVs **122<sub>V</sub>** are similar to TPVs **122<sub>IV</sub>** of FIG. 7A. Third conductive layer **223<sub>V</sub>** is similar to third conductive layer **223<sub>IV</sub>**. First conductive layer **203<sub>V</sub>** is similar to first conductive layer **203<sub>IV</sub>**. Second conductive layer **207<sub>V</sub>** is similar to second conductive layer **207<sub>IV</sub>**. However, a fourth conductive layer **225<sub>V</sub>** is formed between the first conductive layer **223<sub>V</sub>** and the third conductive layer **203<sub>V</sub>** as shown in FIG. 8A. As mentioned above, the third conductive layer **223<sub>V</sub>** is made of Cu or Ti. The fourth conductive layer **225<sub>V</sub>** is made of solder. The thickness  $D_{4V}$  of fourth conductive layer **225<sub>V</sub>** is in a range from about 0.3  $\mu\text{m}$  to about 2  $\mu\text{m}$ , in some embodiments.

The third conductive layer **223<sub>V</sub>**, made of Cu or Ti, is removed by etching when during the removal of plating seed layer **204** as described above. FIG. 8B shows TPVs **122<sub>V</sub>**' after the third conductive layer **223<sub>V</sub>** is removed, in accordance with some embodiments. Recesses **224<sub>V</sub>** is formed. The height  $H_V$  of recesses **224<sub>V</sub>** is in a range from about 0.3  $\mu\text{m}$  to about 2  $\mu\text{m}$ , in some embodiments.

TPVs **122<sub>V</sub>**' are bonded to connectors **117<sub>V</sub>** to form bonding structures **260<sub>V</sub>**, as shown in FIG. 8C in accordance with some embodiments. Solder from connectors **117** fills the recess near the surface of TPVs **122<sub>V</sub>**'. FIG. 8C shows that an IMC later **142<sub>V</sub>** is formed between the first conductive layer **203<sub>V</sub>** and solder of connectors **117<sub>V</sub>**, in accordance with some embodiments. The thickness range of IMC layer **142<sub>V</sub>** is similar to IMC layer **142'** of FIG. 3B.

The additional conductive layers in the TPVs described above are formed by one or more plating processes prior to the main conductive layer. The different plating processes may be performed in an integrated system. The additional manufacturing cost is limited. The recesses at the ends of the TPVs described are formed by additional etching during the removal of plating seed layer. If the conductive layer removed

to form the recesses is made of Cu or Ti, the etch process is just an extension of the plating seed layer removal process. It could just involve additional etch time. If the conductive layer removed is not Cu or Ti, a different etching process is involved. However, the etching to form recesses and the etching to remove the plating seed layer may be performed in an integrated system. The cost of manufacturing related to forming recess is also limited. However, the protective layer of the additional conductive layers, which is less likely to oxidize and less likely to form IMC with solder, improves yield and reliability of bonding structures formed between die package. The recesses also improve yield and reliability of bonding structures formed between die packages.

Various embodiments of mechanisms for forming through package vias (TPVs) with multiple conductive layers and/or recesses in a die package and a package on package (PoP) device with bonding structures utilizing the TPVs are provided. One of the multiple conductive layers acts as a protective layer of the main conductive layer of the TPVs. The protective layer is less likely to oxidize and also has a slower formation rate of intermetallic compound (IMC) when exposed to solder. The recesses in TPVs of a die package are filled by solder from the other die package and the IMC layer formed is below the surface of TPVs, which strengthen the bonding structures.

In some embodiments, a semiconductor die package is provided. The semiconductor die package includes a semiconductor die, and a through package via (TPV) formed in the semiconductor die package. The TPV is disposed next to the semiconductor die, and the TPV include a first conductive layer and a second conductive layer. The first conductive layer fills a first section of the TPV and the second conductive layer fills a second section of the TPV. The semiconductor die package also includes a redistribution structure, and the redistribution structure includes a redistribution layer (RDL). The TPV and the semiconductor die are electrically connected to the RDL and the RDL enables fan-out of the semiconductor die.

In some embodiments, a semiconductor die package is provided. The semiconductor die package includes a semiconductor die, and a through package via (TPV) formed in the semiconductor die package. The TPV is disposed next to the semiconductor die, wherein the TPV include a conductive layer and a recess. The semiconductor die package also includes a redistribution structure, and the redistribution structure includes a redistribution layer (RDL). The TPV and the semiconductor die are electrically connected to the RDL and the RDL enables fan-out of the semiconductor die. The recess is on the opposite side of the conductive layer from the RDL.

In yet some other embodiments, a package-on-package (PoP) device is provided. The PoP device includes a first die package. The first die package includes a first semiconductor die, and a through package via (TPV). The TPV is disposed next to the semiconductor die, and the TPV includes a first conductive layer and a second conductive layer. The PoP device also includes a second die package. The second die package includes a second semiconductor die, and an external connector containing solder. The external connector of the second die package is bonded to the TPV of the first die package.

Although the embodiments and their advantages have been described in detail, it should be understood that various changes, substitutions and alterations can be made herein without departing from the spirit and scope of the embodiments as defined by the appended claims. Moreover, the scope of the present application is not intended to be limited

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to the particular embodiments of the process, machine, manufacture, and composition of matter, means, methods and steps described in the specification. As one of ordinary skill in the art will readily appreciate from the disclosure, processes, machines, manufacture, compositions of matter, means, methods, or steps, presently existing or later to be developed, that perform substantially the same function or achieve substantially the same result as the corresponding embodiments described herein may be utilized according to the disclosure. Accordingly, the appended claims are intended to include within their scope such processes, machines, manufacture, compositions of matter, means, methods, or steps. In addition, each claim constitutes a separate embodiment, and the combination of various claims and embodiments are within the scope of the disclosure.

What is claimed is:

1. A semiconductor die package, comprising:

- a semiconductor die, the semiconductor die having a topmost surface and having a contact pad on a bottommost surface;
  - a molding compound at least partially encapsulating the semiconductor die, the molding compound having a topmost surface and a bottommost surface, the topmost surface of the molding compound being coplanar with the topmost surface of the semiconductor die;
  - a through package via (TPV) formed in the molding compound the TPV having a bottommost end that is coplanar with the bottommost surface of the molding compound and having a topmost end that is co-planar with the topmost surface of the molding compound, wherein the TPV has a substantially uniform diameter from the topmost end of the TPV to the bottommost end of the TPV and includes a first conductive layer and a second conductive layer, and wherein the first conductive layer contacts a surface of the molding compound at a first side, contacts the surface of the molding compound at a second side, and is planar across a top surface defined by the first and second side; and
  - a redistribution structure, wherein the redistribution structure includes a redistribution layer (RDL), wherein the TPV is physically connected to the RDL in a first plane, the first plane being parallel to the bottommost surface of the semiconductor die and wherein the semiconductor die is also physically connected to the RDL in the first plane and wherein both the TPV and the semiconductor die are electrically connected to the RDL and wherein the RDL enables fan-out of the semiconductor die.
2. The semiconductor die package of claim 1, wherein the first conductive layer has a height in a range from about 0.1  $\mu\text{m}$  to about 30  $\mu\text{m}$ .
3. The semiconductor die package of claim 1, wherein the second conductive layer has a height in a range from about 50  $\mu\text{m}$  to about 300  $\mu\text{m}$ .
4. The semiconductor die package of claim 1, wherein there is a third conductive layer formed next to the first conductive layer and opposite the second conductive layer.
5. The semiconductor die package of claim 4, wherein the third conductive layer is made of solder.
6. The semiconductor die package of claim 1, wherein the first conductive layer is made of a conductive metal less likely to oxidize and to form intermetallic compound (IMC) than copper when bonded to solder.
7. The semiconductor die package of claim 1, wherein the first conductive layer is made of a metal selected from a group consisting of Ni, Pt, Sn, and Sn alloy, wherein the Sn alloy contains Ag, Cu, Bi, and combinations thereof.
8. The semiconductor die package of claim 1, wherein the second conductive layer is made of copper.

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9. The semiconductor die package of claim 1, wherein the first conductive layer is a different material than the second conductive layer.

10. A semiconductor die package, comprising:

- a semiconductor die;
- a through package via (TPV) formed in a molding compound of the semiconductor die package, wherein the TPV is disposed next to the semiconductor die, wherein the TPV extends from a topmost surface of the molding compound to a bottommost surface of the molding compound and has a substantially uniform diameter from the topmost surface of the molding compound to the bottommost surface of the molding compound and includes a conductive layer having a first end that is co-planar with the bottommost surface of the molding compound, a protective layer in contact with a second end of the conductive layer opposite the first end, and a solder layer having a first end that is in contact with the protective layer and having a second end that is co-planar with the topmost surface of the molding compound; and
- a redistribution structure, wherein the redistribution structure includes a redistribution layer (RDL) extending along a common plane, wherein the TPV and the semiconductor die are electrically connected to the RDL and both the TPV and the semiconductor die are physically connected to the RDL in the same common plane, and wherein the RDL enables fan-out of the semiconductor die.

11. A package-on-package (PoP) device, comprising:

- a first die package, wherein the first die package comprises:
  - a first semiconductor die having a major surface and being embedded in a molding compound and having a topmost surface that is coplanar with a topmost surface of the molding compound, the first semiconductor die also having a contact pad on a bottommost surface of the first semiconductor die, and
  - a through package via (TPV), wherein the TPV is disposed next to the semiconductor die, wherein the TPV includes a first conductive layer and a second conductive layer, wherein the first conductive layer comprises a plurality of protective layers, and wherein the first conductive layer contacts the topmost surface of the molding compound at a first side, contacts a bottommost surface of the molding compound at a second side, and is planar across a top surface defined by the first and second side, and wherein the first conductive layer and the second conductive layer have the same diameter, and wherein the TPV has a first end that is co-planar with the bottommost surface of the molding compound and has a second end that is co-planar with the topmost surface of the molding compound;
- a redistribution structure including a planar redistribution layer that physically and electrically contacts both the TPV and the contact pad of the first semiconductor die in a common plane, the common plane being parallel to the major surface of the semiconductor die and
- a second die package, wherein the second die package comprises:
  - a second semiconductor die, and
  - an external connector containing solder,
 wherein the external connector of the second die package is bonded to the TPV of the first die package.

12. The PoP device of claim 11, wherein the external connectors of the second die package are bonded to the first conductive layer of the TPV.

13. The PoP device of claim 11, wherein an intermetallic compound (IMC) is formed between the external connector and the first conductive layer, wherein the IMC has a thickness in a range from about 0.5  $\mu\text{m}$  to about 10  $\mu\text{m}$ .

14. The PoP device of claim 11, wherein the first die package further comprises:

a redistribution structure, wherein the redistribution structure includes a redistribution layer (RDL), wherein the TPV and the semiconductor die are electrically connected to the RDL and the wherein RDL enables fan-out of the semiconductor die. 5

15. The PoP device of claim 11, wherein the first conductive layer of the TPV is removed from the TPV prior to bonding with the external connector, and wherein the second conductive layer is made of solder. 10

16. The PoP device of claim 11, wherein the first conductive layer is made of a conductive metal less likely to oxidize and to form intermetallic compound (IMC) than copper when bonded to solder. 15

17. The PoP device of claim 11, wherein the first conductive layer is made of a metal selected from a group consisting of Ni, Pt, Sn, and Sn alloy, wherein the Sn alloy contains Ag, Cu, Bi, and combinations thereof.

18. The PoP device of claim 11, wherein the second conductive layer is made of copper. 20

19. The PoP device of claim 11, wherein the first conductive layer has a height in a range from about 0.1  $\mu\text{m}$  to about 30  $\mu\text{m}$ .

20. The PoP device of claim 11, wherein the second conductive layer has a height in a range from about 50  $\mu\text{m}$  to about 300  $\mu\text{m}$ . 25

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